

2A, 50V - 600V Surface Mount Super Fast Rectifier

FEATURES

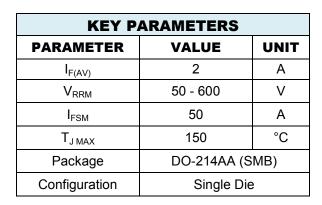
- Glass passivated junction chip
- Ideal for automated placement
- Low profile package
- Super fast recovery time for high efficiency
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- Converter

MECHANICAL DATA

- Case: DO-214AA (SMB)
- Molding compound meets UL 94V-0 flammability rating
- Packing code with suffix "G" means green compound (halogen-free)
- Part no. with suffix "H" means AEC-Q101 qualified
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.09 g (approximately)







DO-214AA (SMB)

PARAMETER	SYMBOL	ES2A	ES2B	ES2C	ES2D	ES2F	ES2G	ES2H	ES2J	UNIT
Marking code on the device		ES2A	ES2B	ES2C	ES2D	ES2F	ES2G	ES2H	ES2J	
Repetitive peak reverse voltage	V_{RRM}	50	100	150	200	300	400	500	600	V
Reverse voltage, total rms value	$V_{R(RMS)}$	30	70	105	140	210	280	350	420	V
Maximum DC blocking voltage	V_{DC}	50	100	150	200	300	400	500	600	V
Forward current	I _{F(AV)}	2			Α					
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	50				А				
Junction temperature	T _J	T _J - 55 to +150			°C					
Storage temperature	T _{STG}	- 55 to +150			°C					

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ES2A - ES2JTaiwan Semiconductor

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Lead Thermal Resistance	$R_{\Theta JL}$	20	°C/W		
Junction to Ambient Thermal Resistance	R _{eJA}	75	°C/W		

PARAMETER		CONDITIONS	SYMBOL	TYP	MAX	UNIT
	ES2A		V _F	-	0.95	V
	ES2B			-		V
	ES2C			-		V
(1)	ES2D	I _F = 2A,T _J = 25°C		-		V
Forward voltage per diode (1)	ES2F			-	1.30	V
	ES2G			-		V
	ES2H			-	1.70	V
	ES2J			-		V
Reverse current @ rated V _R per diode ⁽²⁾		T _J = 25°C		-	10	μΑ
		T _J = 125°C	l _R	-	350	μΑ
	ES2A	1 MHz, V _R =4.0V	CJ	25	-	pF
	ES2B				-	pF
	ES2C				-	pF
	ES2D				-	pF
Junction capacitance	ES2F			20	-	pF
	ES2G				-	pF
	ES2H				-	pF
	ES2J				-	pF
Reverse recovery time		I _F =0.5A ,I _R =1.0A I _{RR} =0.25A	t _{rr}	-	35	ns

Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms



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ORDERING INFORMATION							
PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX(*)	PACKAGE	PACKING		
	Н	R5	G	SMB	850 / 7" Plastic reel		
ES2x (Note 1)		R4		SMB	3,000 / 13" Paper reel		
(14010-1)		M4		SMB	3,000 / 13" Plastic reel		

Note:

^{*:} Optional available

EXAMPLE P/N						
EXAMPLE P/N	PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION	
ES2JHR5G	ES2J	Н	R5	G	AEC-Q101 qualified Green compound	

^{1. &}quot;x" defines voltage from 50V (ES2A) to 600V (ES2J)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig1. Forward Current Derating Curve

3 AVERAGE FORWARD CURRENT (A) 2 1 RESISTER OR INDUCTIVE LOAD 0 110 120 90 100 130 150 80 140 LEAD TEMPERATURE (°C)

Fig2. Typical Junction Capacitance

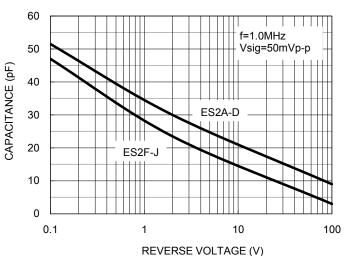


Fig3. Typical Reverse Characteristics

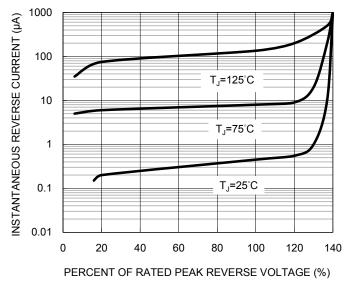
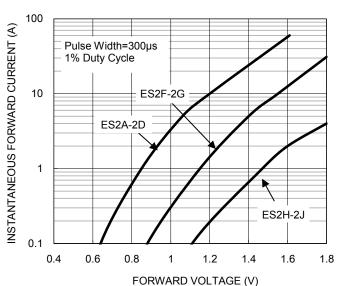


Fig4. Typical Forward Characteristics



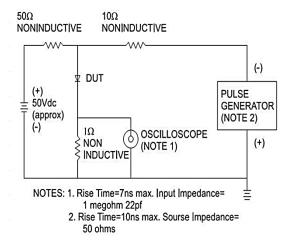
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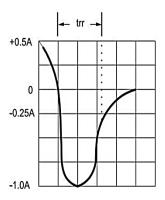


Fig5. Maximum Non-repetitive Forward Surge Current



Fig6. Reverse Recovery Time Characteristic And Test Circuit Diagram

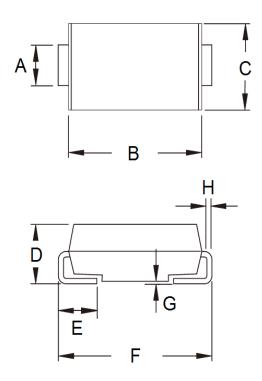






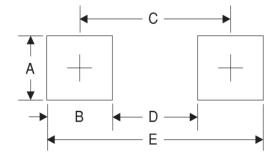
PACKAGE OUTLINE DIMENSIONS

DO-214AA (SMB)



DIM.	Unit	(mm)	Unit (inch)		
DIIVI.	Min	Max	Min	Max	
Α	1.95	2.20	0.077	0.087	
В	4.05	4.60	0.159	0.181	
С	3.30	3.95	0.130	0.156	
D	1.95	2.65	0.077	0.104	
Е	0.75	1.60	0.030	0.063	
F	5.10	5.60	0.201	0.220	
G	0.05	0.20	0.002	0.008	
Н	0.15	0.31	0.006	0.012	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	2.3	0.091
В	2.5	0.098
С	4.3	0.169
D	1.8	0.071
Е	6.8	0.268

MARKING DIAGRAM



P/N = Marking Code G = Green Compound YW = Date Code F = Factory Code





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